















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	MJL21195G
Overseas Part Number	MJL21195G
▶ Equivalent Part Number	MJL21195G





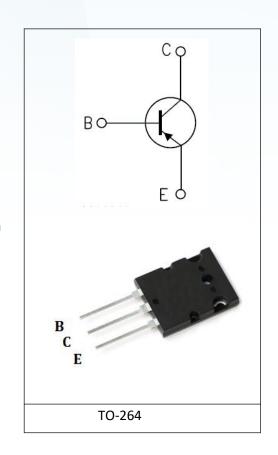
Transistor Silicon PNP Epitaxial Type

MJL21195

Power Amplifier Applications

- Complementary to MJL21196
- High collector voltage:VCEO=-250V (min)
- Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Absolute Maximum Ratings(Tc=25 $^{\circ}$ C):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{СВО}	-400	V
Collector-emitter voltage	VCEO	-250	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	lc	-16	А
Base current	I _B	-5	А
Collector power dissipation (Tc=25°C)	Pc	230	W
Junction temperature	T j	150	$^{\circ}$
Storage temperature range	Тѕтс	-55~150	$^{\circ}$



Electrical Characteristics (Tc=25 $^{\circ}$ C):

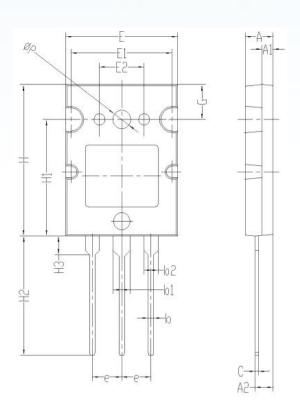
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
Collector cut-off current	Ісво	V _{CB} =-250V; I _E =0			-10.0	uA
Emitter cut-off current	ІЕВО	V _{EB} =-5V; I _c =0			-10.0	uA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-50mA;I _B =0	-250			V
	hfe	V _{CE} =-5V; I _C =-8A;	20		80	
DC current gain	h _{FE(2)}	VcE=-5V; Ic=-16A;	8			
Collector-emitter saturation voltage	Vce(sat)	Ic=-8А; Iв=-0.8А			-1.4	V
	V _{CE} (sat)	Ic=-16А; Iв=-3.2А			-4	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V;I _C =-8A			-2.2	V
Transition frequency	f⊤	V _{CE} =-10V; I _C =-1A	4			MHz

Symbol	Paramter	Тур	Units
$R_{ heta JC}$	Junction-to-Case	0.63	°C/W



Package Information

TO-264 PACKAGE



Symbol	Dimensions(millimeters)		
Symbol	Min.	Max.	
Α	4.80	5.20	
A1	1.80	2.20	
A2	3.00	3.40	
b	0.80	1.20	
b1	2.80	3.20	
b2	2.30	2.70	
С	0.40	0.80	
е	5.25	5.65	
Е	19.8	20.2	
E1	17.8	18.2	
E2	7.8	8.2	
Н	25.8	26.2	
H1	19.8	20.2	
H2	20.0	21.0	
H3	3.05	3.45	
G	5.80	6.20	
ΦР	3.10	3.50	
J	4.80	5.20	
K	1.80	2.20	



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